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IGBT

SGH80N60UF

Ultra-Fast IGBT

General Description

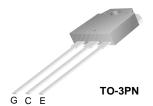
Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.1 \text{ V } @ I_C = 40 \text{A}$
- · High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		SGH80N60UF	Units
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T _C = 25°C	80	Α
IC	Collector Current	@ T _C = 100°C	40	Α
I _{CM (1)}	Pulsed Collector Current		220	Α
I _F	Diode Continuous Forward Current	@ T _C = 100°C	25	Α
I _{FM}	Diode Maximum Forward Current		280	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	195	W
	Maximum Power Dissipation	@ T _C = 100°C	78	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes:(1) Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.64	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250uA$	600			V
$\Delta B_{VCES}/$ ΔT_J	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V$, $I_C = 1mA$		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA
On Cha	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 40 \text{mA}, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
	Collector to Emitter	$I_C = 40A$, $V_{GE} = 15V$		2.1	2.6	V
V _{CE(sat)}	Saturation Voltage	$I_C = 80A$, $V_{GE} = 15V$		2.6		V
Dynami	c Characteristics					
C _{ies}	Input Capacitance	V 20V V 0V		2790		pF
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$ f = 1MHz		350		pF
C _{res}	Reverse Transfer Capacitance			100		pF
	ng Characteristics	1	T.			
t _{d(on)}	Turn-On Delay Time					
t _r				23		ns
	Rise Time	_		50		ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 300 V, I _C = 40A,		50 90	130	
t _{d(off)} t _f	Turn-Off Delay Time Fall Time	$R_G = 5\Omega$, $V_{GE} = 15V$,		50 90 50	130 150	ns ns ns
t _{d(off)} t _f E _{on}	Turn-Off Delay Time Fall Time Turn-On Switching Loss		 	50 90 50 570	130 150	ns ns ns uJ
t _{d(off)} t _f E _{on} E _{off}	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_G = 5\Omega$, $V_{GE} = 15V$,		50 90 50 570 590	130 150 	ns ns ns uJ uJ
t _{d(off)} t _f E _{on} E _{off} E _{ts}	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss	$R_G = 5\Omega$, $V_{GE} = 15V$,	 	50 90 50 570 590 1160	130 150 1500	ns ns ns uJ uJ
t _{d(off)} t _f E _{on} E _{off} E _{ts}	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time	$R_G = 5\Omega$, $V_{GE} = 15V$,	 	50 90 50 570 590 1160 30	130 150 1500	ns ns ns uJ uJ uJ
$t_{d(off)}$ t_{f} E_{on} E_{off} E_{ts} $t_{d(on)}$ t_{r}	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25$ °C	 	50 90 50 570 590 1160 30 55	130 150 1500 	ns ns ns uJ uJ uJ ns
t _{d(off)} t _f E _{on} E _{off} E _{ts} t _{d(on)} t _r	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V}, I_C = 40A,$	 	50 90 50 570 590 1160 30 55 150	130 150 1500 200	ns ns ns uJ uJ uJ ns ns
t _d (off) t _f E _{on} E _{off} Et _s t _d (on) t _r	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 40\text{A,}$ $R_G = 5\Omega$, $V_{GE} = 15V$,	 	50 90 50 570 590 1160 30 55 150	130 150 1500 200 250	ns ns ns uJ uJ uJ ns ns ns
td(off) tf Eon Eoff tts td(on) tr td(off)	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V}, I_C = 40A,$	 	50 90 50 570 590 1160 30 55 150 160 630	130 150 1500 1500 200 250	ns ns ns uJ uJ ns ns ns
td(off) tf Eon Eoff Ets td(on) tr td(off) tf Ets Etd(off) tr Edit Edit Edit Edit Edit Edit Edit Edit	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 40\text{A,}$ $R_G = 5\Omega$, $V_{GE} = 15V$,	 	50 90 50 570 590 1160 30 55 150 160 630 940	130 150 1500 200 250	ns ns ns uJ uJ ns ns ns us uJ uJ us
td(off) tf Eon Eoff Ets td(on) tr td(off) tf Ets	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 40\text{A,}$ $R_G = 5\Omega$, $V_{GE} = 15V$,	 	50 90 50 570 590 1160 30 55 150 160 630 940	130 150 1500 200 250 2000	ns ns ns uJ uJ ns ns ns us uJ
td(off) tf Eon Eoff Ets td(on) tr td(off) tr td(off) tf Eon Eoff Eon Eoff Eon	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Total Gate Charge	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 40\text{A,}$ $R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 125^{\circ}C$	 	50 90 50 570 590 1160 30 55 150 160 630 940	130 150 1500 200 250	ns ns ns uJ uJ ns ns ns us uJ uJ us
td(off) tf Eon Eoff Ets td(on) tr td(off) tf Eon Eoff td Con Eoff Eon Eoff Eon Eoff Eon Eoff Eoff	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Total Gate Charge Gate-Emitter Charge	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V}$, $I_C = 40A$, $R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 125^{\circ}C$ $V_{CE} = 300 \text{ V}$, $I_C = 40A$,	 	50 90 50 570 590 1160 30 55 150 160 630 940	130 150 1500 200 250 2000	ns ns ns uJ uJ ns ns ns us uJ
td(off) tf Eon Eoff Ets td(on) tr td(off) tr td(off) tg td(off) tg Con Eoff Eon Con Con Con Con Con Con Con Con Con C	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Total Gate Charge	$R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 40\text{A,}$ $R_G = 5\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 125^{\circ}C$		50 90 50 570 590 1160 30 55 150 160 630 940 1580	130 150 1500 200 250 2000 250	ns ns ns uJ uJ ns ns ns us ns ns ns ns ns ns

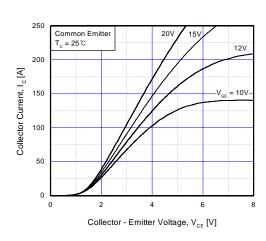


Fig 1. Typical Output Characteristics

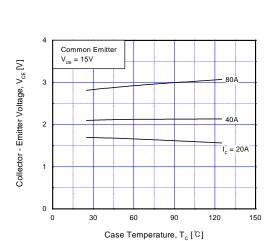


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

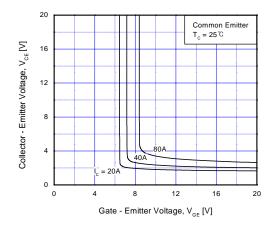


Fig 5. Saturation Voltage vs. V_{GE}

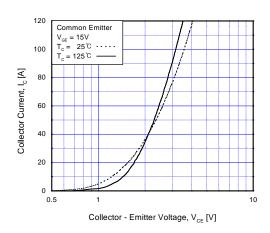


Fig 2. Typical Saturation Voltage Characteristics

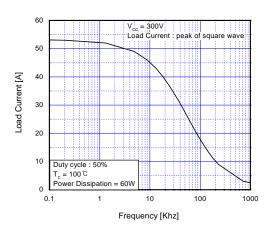


Fig 4. Load Current vs. Frequency

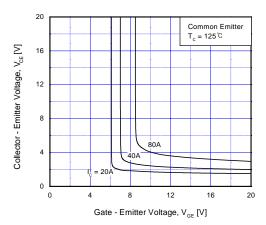
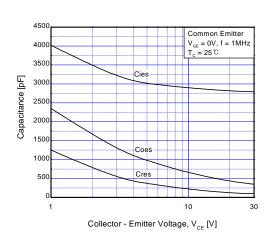


Fig 6. Saturation Voltage vs. $V_{\rm GE}$

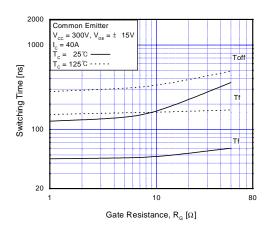
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Common Emitter $V_{cc} = 300V, V_{cg} = \pm 15V$ $V_{cc} = 40A$ $V_{cc} = 25\,^\circ\text{C}$ $V_{cc} = 125\,^\circ\text{C}$ $V_{$

Fig 7. Capacitance Characteristics

Fig 8. Turn-On Characteristics vs.
Gate Resistance



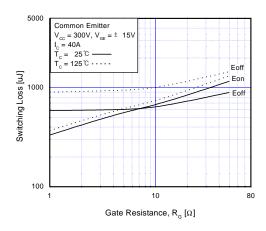
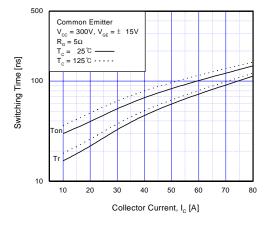


Fig 9. Turn-Off Characteristics vs.
Gate Resistance

Fig 10. Switching Loss vs. Gate Resistance



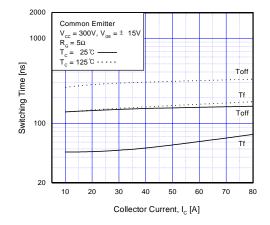
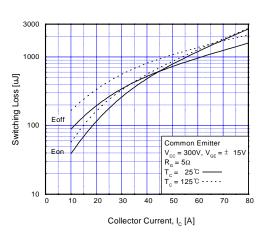


Fig 11. Turn-On Characteristics vs. Collector Current

Fig 12. Turn-Off Characteristics vs.
Collector Current



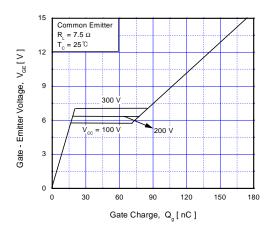
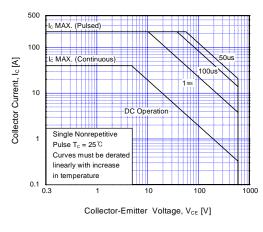


Fig 13. Switching Loss vs. Collector Current

Fig 14. Gate Charge Characteristics



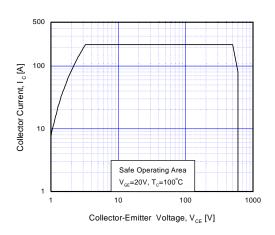


Fig 15. SOA Characteristics

Fig 16. Turn-Off SOA Characteristics

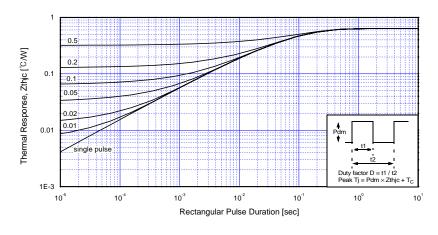
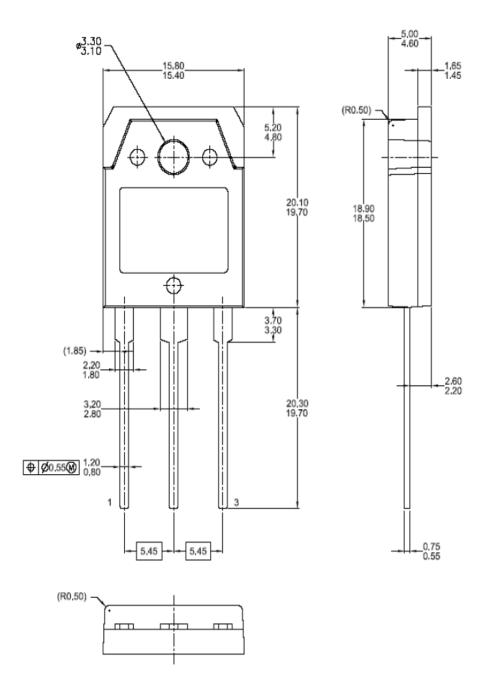


Fig 17. Transient Thermal Impedance of IGBT

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Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

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